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Baker

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 (45) **Date of Patent: Jun. 10, 2003**

(54) **SENSING METHOD AND APPARATUS FOR RESISTANCE MEMORY DEVICE**

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* cited by examiner

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(*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 34 days.

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(21) Appl. No.: **09/939,655**

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(65) **Prior Publication Data**

US 2003/0043616 A1 Mar. 6, 2003

(51) **Int. Cl.**⁷ **G11C 11/00**

(52) **U.S. Cl.** **365/148; 365/158**

(58) **Field of Search** 365/148, 158, 365/171, 173, 207, 209

(56) **References Cited**

U.S. PATENT DOCUMENTS

6,128,239 A 10/2000 Perner 365/209

(57) **ABSTRACT**

An MRAM memory integrated circuit is disclosed. Resistance, and hence logic state, is determined by discharging a first charged capacitor through an unknown cell resistive element to be sensed at a fixed voltage, and a pair of reference capacitors. The rate at which the parallel combination of capacitors discharge is between the discharge rate associated with a binary '1' and '0' value, and thus offers a reference for comparison.

35 Claims, 7 Drawing Sheets

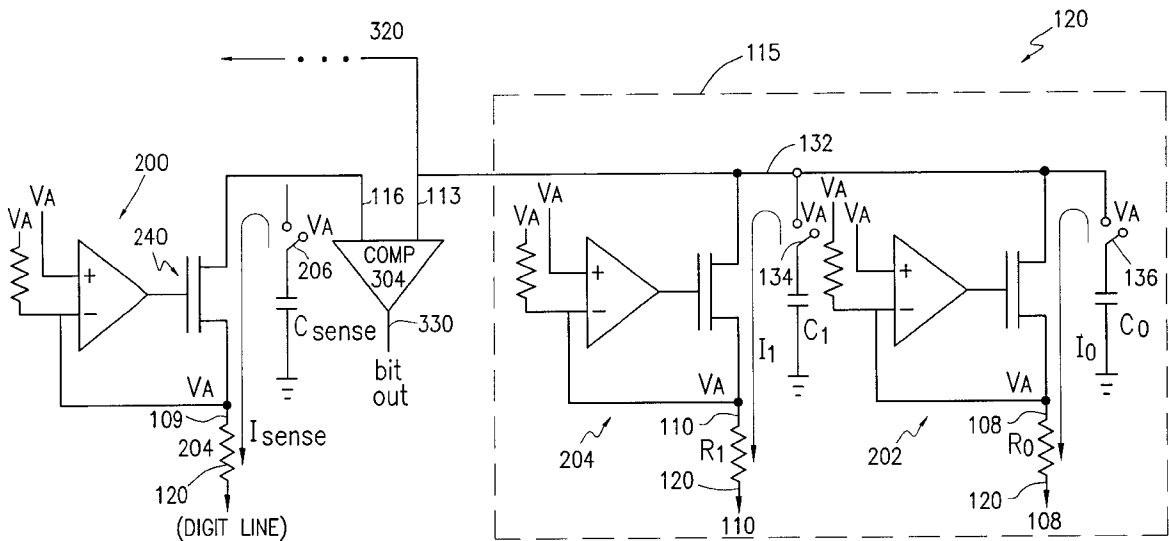


FIG. 1

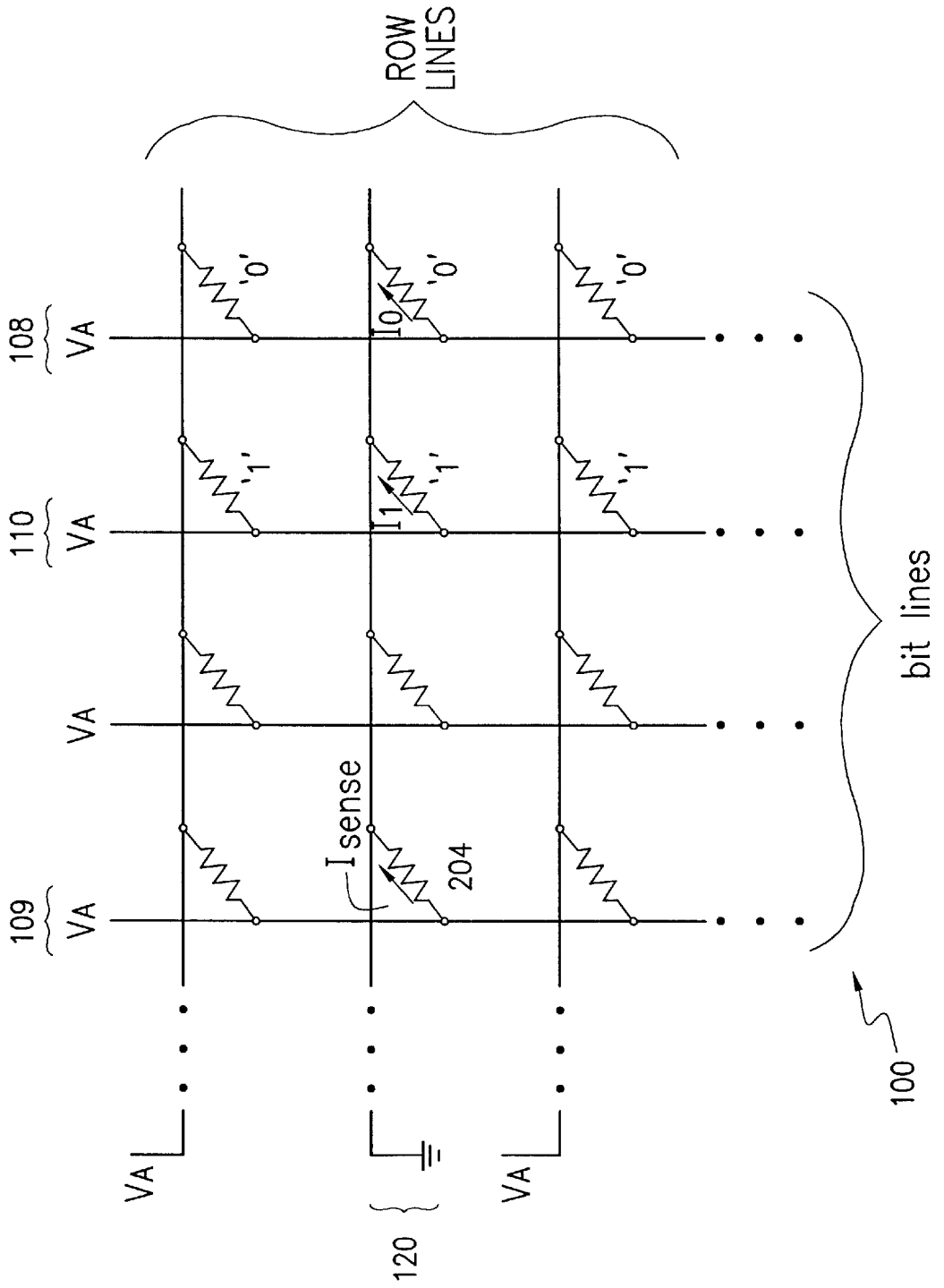
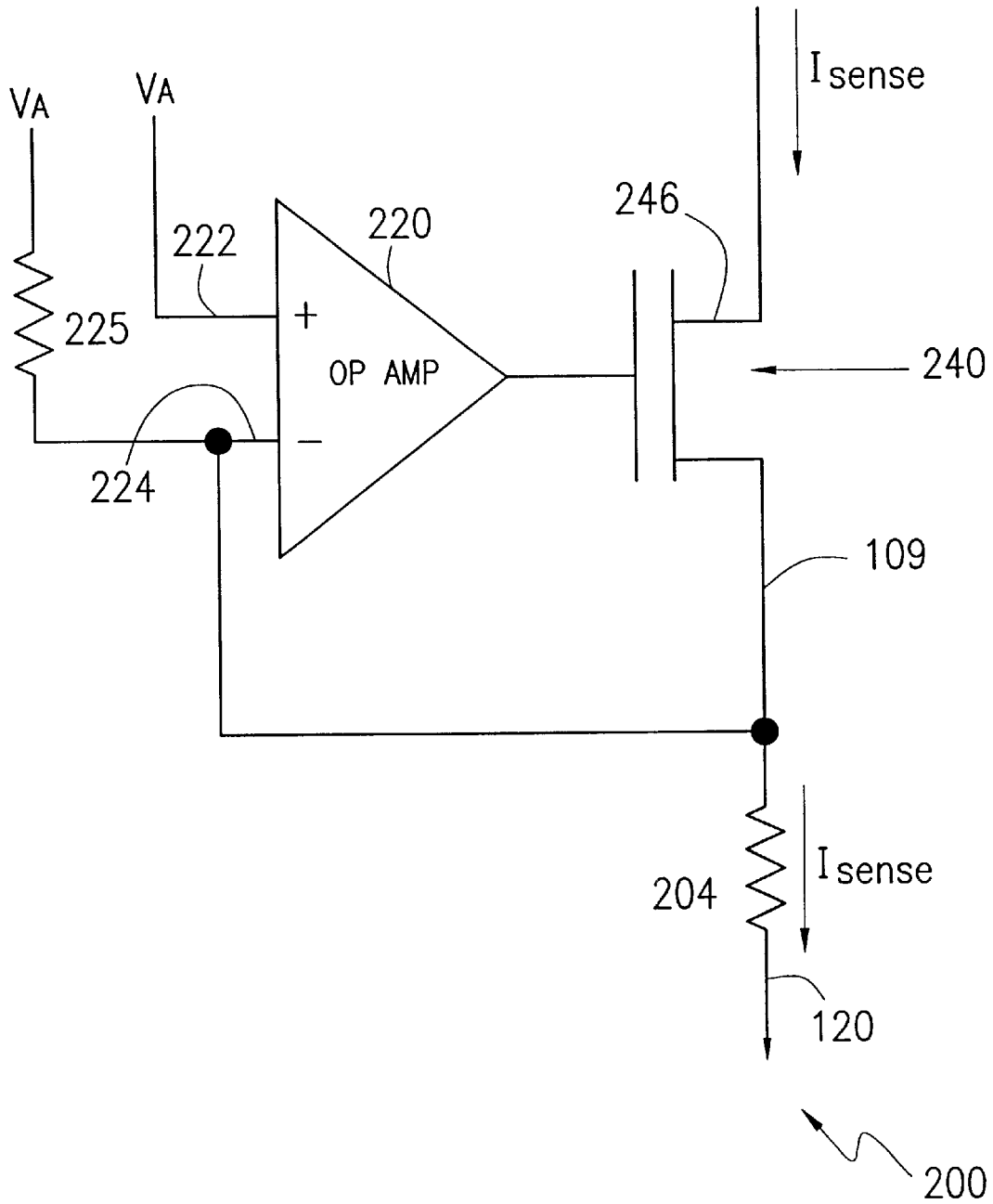


FIG. 2



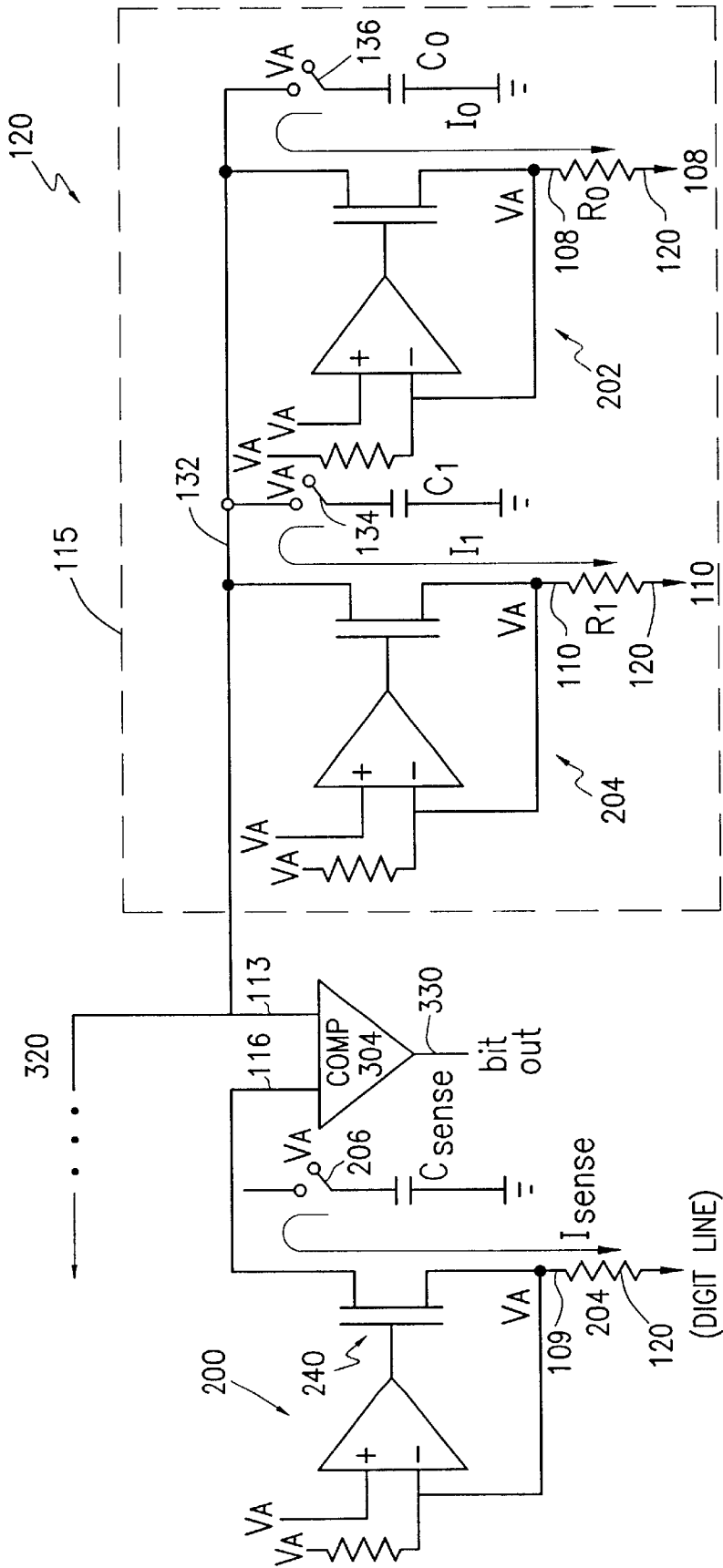


FIG. 3

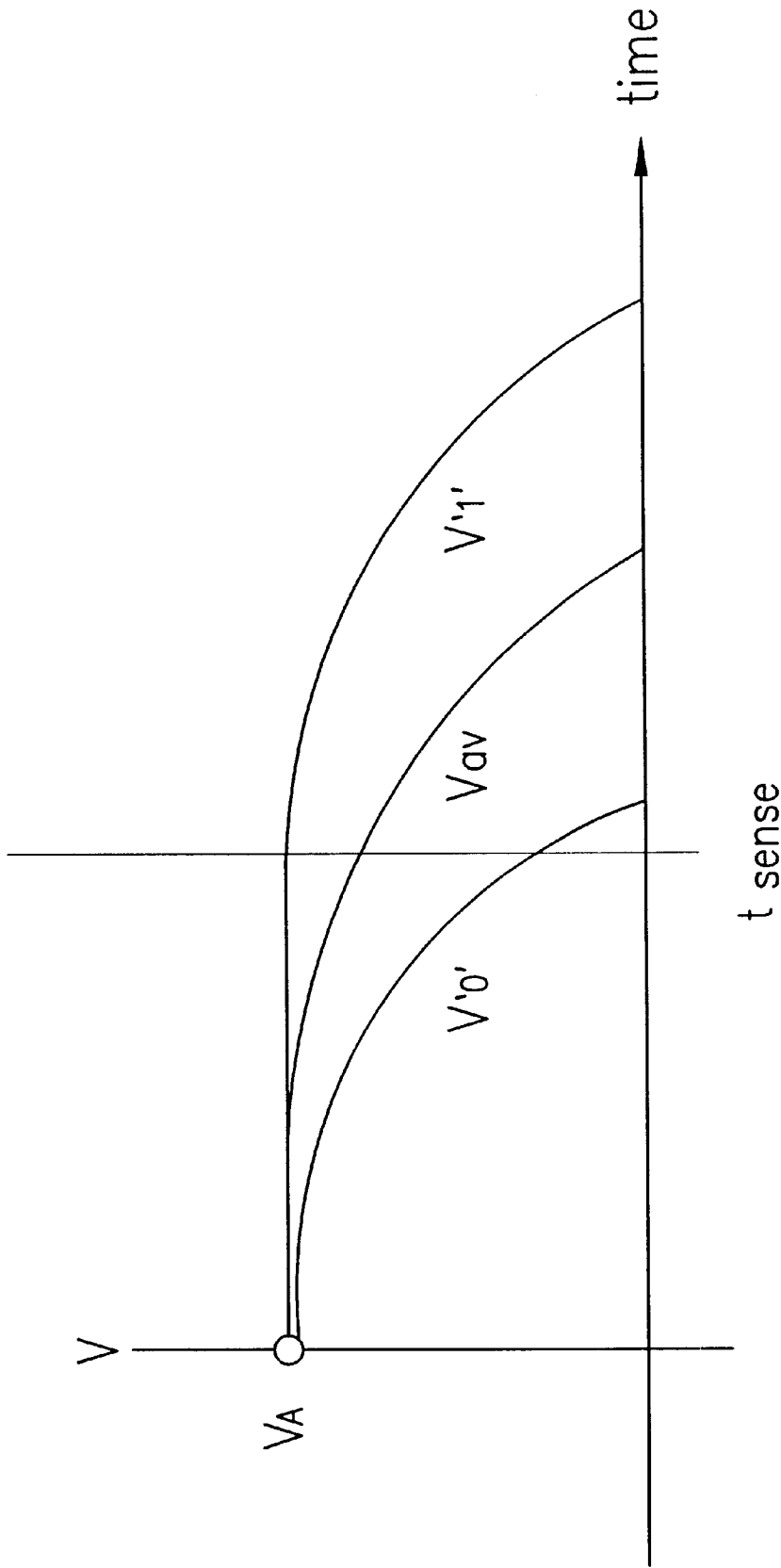


FIG. 4

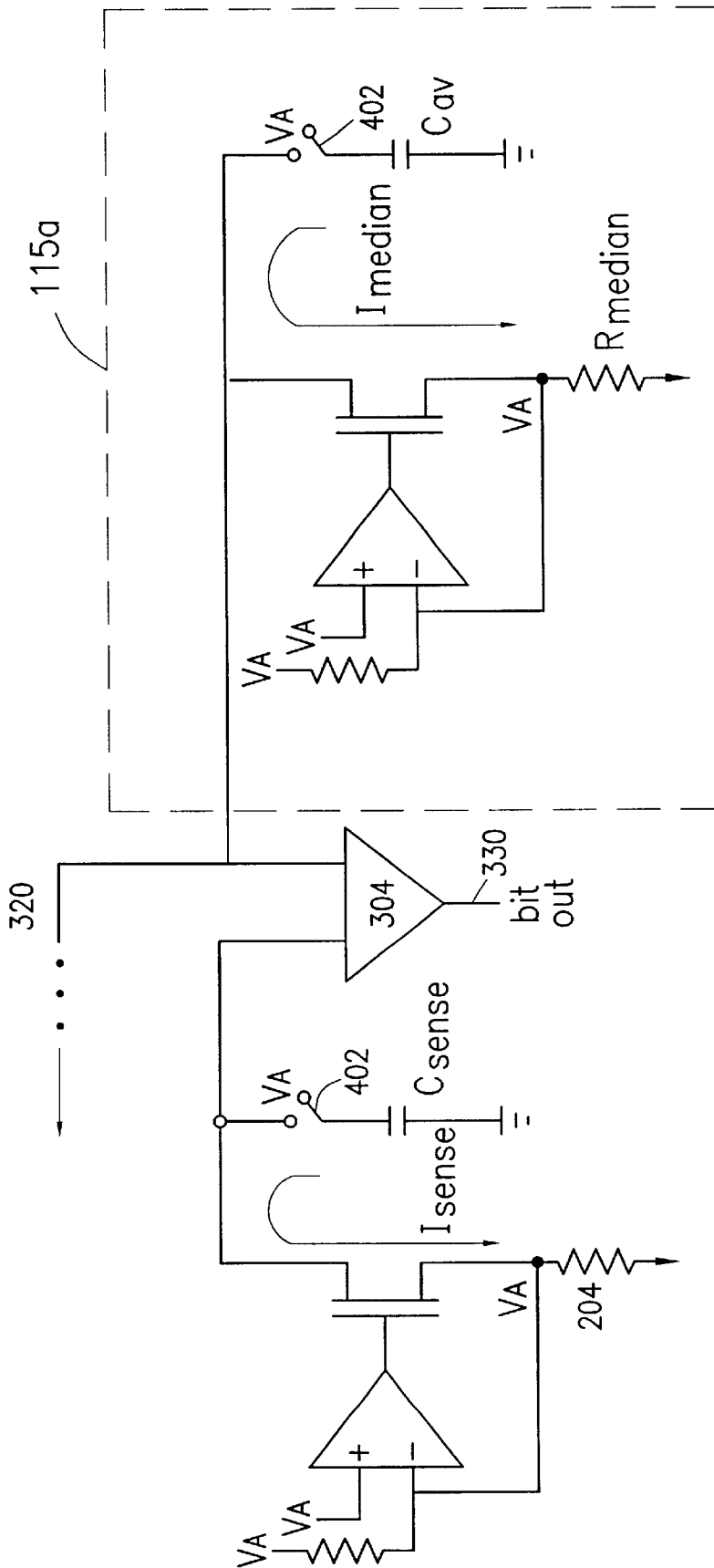


FIG. 5

FIG. 6

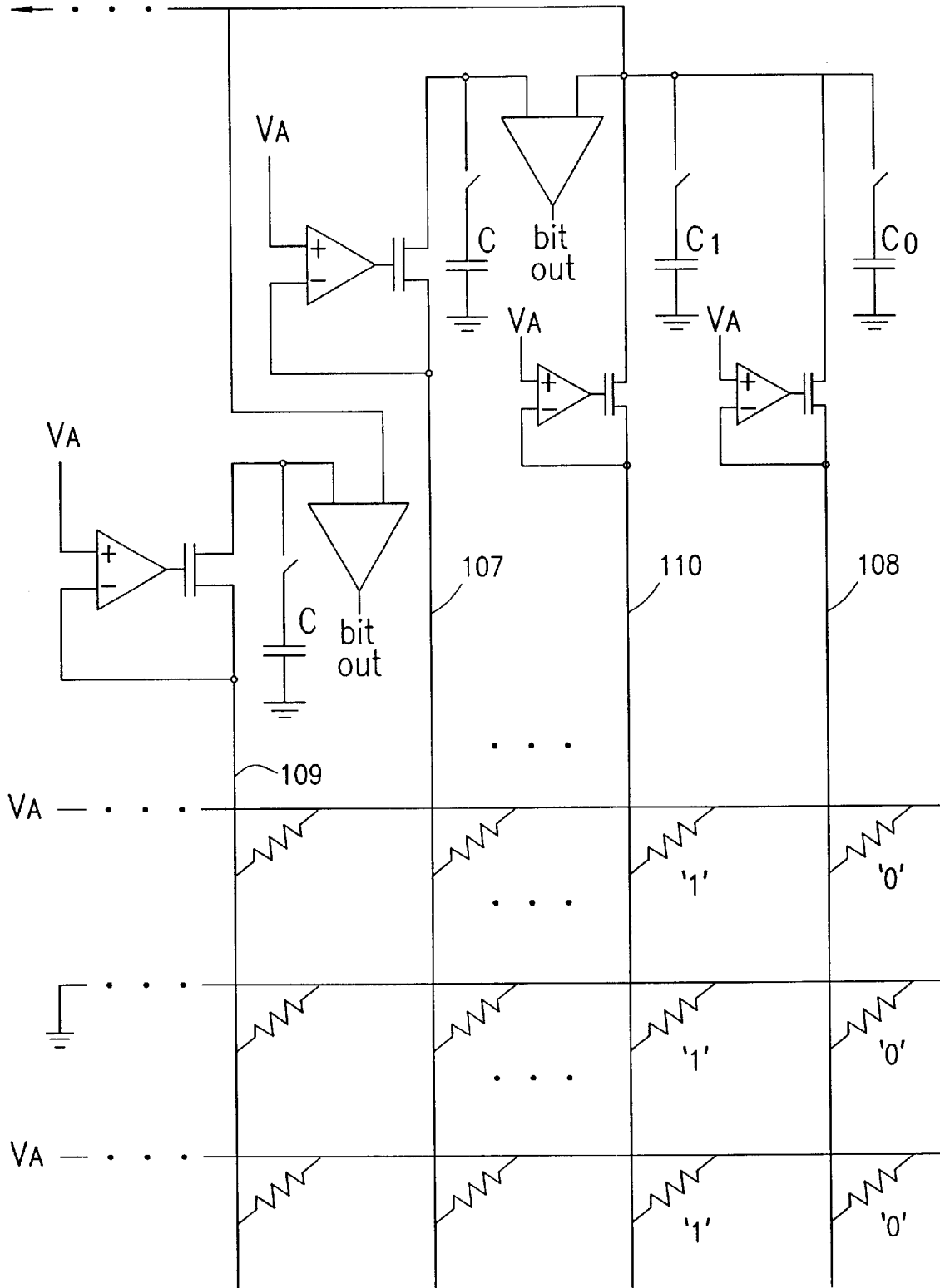
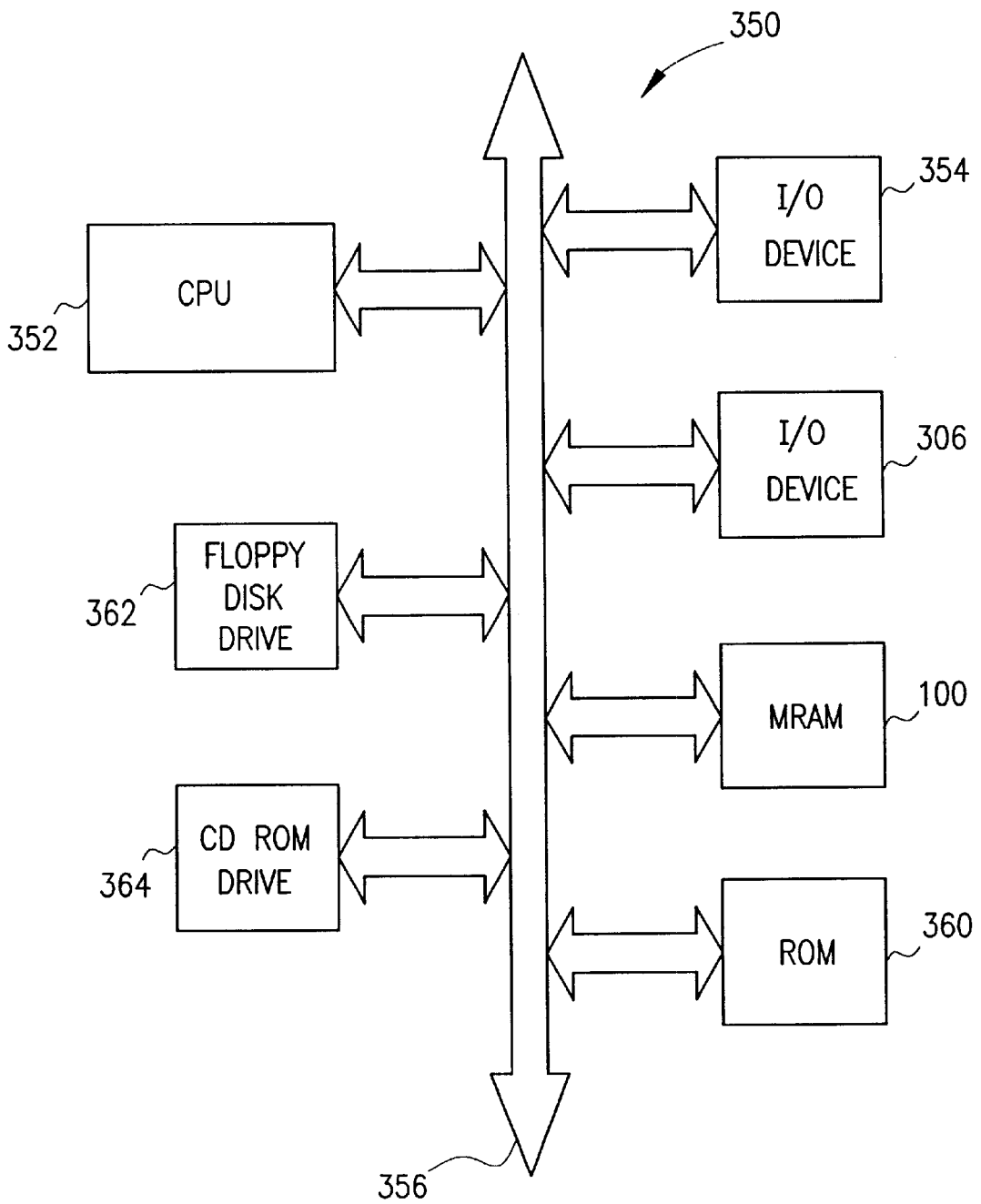


FIG. 7



SENSING METHOD AND APPARATUS FOR RESISTANCE MEMORY DEVICE

FIELD OF THE INVENTION

The present invention relates to the field of resistor-based memory circuits. More particularly, it relates to a method for precisely sensing the resistance value of a resistor-based memory cell, for example, a Magnetic Random Access Memory (MRAM) magnetic memory cell.

BACKGROUND OF THE INVENTION

A resistor-based memory such as a magnetic random access memory (MRAM) typically includes an array of resistor-based magnetic memory cells. The logic state of such a magnetic memory cell is indicated by its resistance. One resistance value, e.g., the higher value, may be used to signify a logic high while another resistance value, e.g., the lower value, may be used to signify a logic low. The value stored in each memory cell can be determined by measuring the resistance value of the cell to determine whether the cell corresponds to a logic high or low. Such direct measurements are often difficult to simply and easily implement and require a number of comparators which increases the cost and size of the memory circuit. A simplified, more reliable method of sensing the resistance value of a resistor-based memory cell is desired.

SUMMARY OF THE INVENTION

The present invention provides a simple and reliable method and apparatus for sensing the logic state of a resistor-based memory cell. Resistance is measured by first charging a first capacitor to a predetermined voltage, discharging the first capacitor through a resistance to be measured while discharging a second capacitor through an associated reference resistance of known value and comparing the discharge characteristics e.g. the discharge voltage of two capacitors to determine a value of resistance to be measured relative to the reference resistance.

In one exemplary embodiment, a pair of second capacitors are used, each discharging through an associated reference resistance, one having a value corresponding to one possible resistance value of the resistance to be measured and the other having a value corresponding to another possible resistance value of the resistance to be measured. The combined discharge characteristics of the pair of second capacitors, e.g. an average of the discharge capacitor voltage, is compared with the discharge characteristics e.g. the discharge voltage of the first capacitor to determine a value of the resistance to be measured relative to an average value of the two reference resistances.

BRIEF DESCRIPTION OF THE DRAWINGS

The foregoing and other features and advantages of the invention will become more apparent from the detailed description of the exemplary embodiments of the invention given below with reference to the accompanying drawings in which:

FIG. 1 shows the invention employed in an exemplary MRAM device;

FIG. 2 shows a schematic diagram of one aspect of the invention;

FIG. 3 shows a schematic diagram of an additional aspect of the invention;

FIG. 4 shows the discharge rate characteristics of capacitors employed in the invention;

FIG. 5 shows a schematic diagram of an additional aspect of the invention;

FIG. 6 shows a schematic diagram of an additional aspect of the invention; and

FIG. 7 shows the invention utilized in a computer system.

DETAILED DESCRIPTION OF THE INVENTION

A portion of a MRAM array **100** with which the present invention may be used is shown in FIG. 1. The logical state of an MRAM memory element e.g. **204** is represented by the resistance of that element. In the present invention, resistance is determined by holding a voltage constant across a cell's resistive element and comparing a voltage produced by the current that flows through that resistive element with a voltage produced by the current flow through a known reference resistance. To read the binary state of a memory cell element, the absolute magnitude of resistance need not be known; only whether the resistance is above or below a value that is intermediate to the logic high and logic low values. Accordingly, to provide a reference current flow for comparison purposes the resistive elements within rightmost column **108** of array **100** are preprogrammed to hold all '0' values, while those within column **110** immediately to its left are preprogrammed to hold all '1' values. The current flowing through these two columns when a particular row line of the array **100** is selected by grounding a rowline, e.g. rowline **120**, will heretofore be designated as I_0 and I_1 , as shown in FIG. 1.

During the reading process, all column and row lines are driven with the same array voltage V_A , except for the one row line, e.g. **120** that is desired to be read. That row line **120** is driven to ground. When row **120** is grounded, a resistive element of a selected column, e.g. column **109**, can be read by a sensing circuit **300** described below. As shown in FIG. 1, both ends of all resistive elements not being measured are maintained at the same potential, V_A . Thus, unwanted current flow through these resistive elements due to "sneak" resistance is negligible. A current I_{sense} flows through the grounded resistive element of a selected column within the row **120** for allowing measurement of the resistance by the sensing circuit **300** (not shown in FIG. 1).

FIG. 2 shows a circuit **200** for regulating current through and voltage across a resistive element **204** being measured. An operational amplifier **220** has one terminal **222** connected to V_A , while the other terminal **224** is connected to the column line **109** for the resistance element **204** which is being sensed. The gate **242** of NMOS transistor **240** is connected to the output of operational amplifier **220**. The source **246** of transistor **240** is connected to one terminal of the resistive element **204** being read, while the other terminal of resistive element **204** is driven to ground by the grounding of wordline **120** described earlier. Operational amplifier **220** and transistor **240** act in concert to keep one terminal of resistive element **204** stably at V_A despite the fact that the other terminal is grounded. In this way, I_{sense} can flow through transistor **240** and resistive element **204**, while current lost through sneak resistor **225** is minimized.

To sense the amount of resistance of resistance element **204**, the current flow through resistance element **204** must be determined, since the voltage across resistance element **204** is held constant at V_A . FIG. 3 shows how the current regulating circuit **200** combined with a voltage comparator **304**, and a reference voltage generating circuit **115** to provide a method and apparatus for determining current flow through sensed resistance element **204**. As shown in FIG. 3,

the active wordline **120** is also connected to reference resistance elements **R0** and **R1** associated with column lines **108** and **110**, which are pre-set to '0' and '1' resistance values respectively. Each column line of array **110** which has resistance elements which may be written to or read has its own sensing circuit and comparator which are active when the column is addressed to select with the grounded rowline, which resistive memory element within a given row is being read. Thus, connection line **320** shows how the reference voltage generating circuit **115** is connected to other columns of array **100**. As noted, each column line (e.g. **109** shown in FIG. 3.) has a voltage having a reference input **113** and sensed voltage input **116**.

The reference voltage generating circuit **115** includes a first **202** and second **204** regulating circuit each associated with a respective reference resistance element **108**, **110**. These regulating circuits respectively hold the voltage across reference resistors elements **108** and **110** at V_A in the manner described above with reference to FIG. 2. The resistance elements R_0 , R_1 have respective known resistance values corresponding to one of the logic states of a memory element and the other corresponding to the other possible logic state. The reference voltage generating circuit **115** also includes capacitors C_1 and C_0 respectively associated with the reference resistance elements R_0 and R_1 . Each of the capacitors C_1 and C_0 has one lower terminal grounded and the other upper terminal connectable to a common voltage line **132** through a respective switch element **134**, **136**. The switch elements **134**, **136** are configured to connect the upper terminals of the capacitors C_1 , C_0 to either a source of voltage V_A or to the common voltage line **132**. The common voltage line **132** is connected to the reference voltage input **113** of comparator **304**.

As noted, the comparator **304** also has a voltage input **116**. This is connected through another switch element **206** to an upper terminal of a sensing capacitor C_{sense} , the lower terminal of which is grounded. Switch element **206** is adapted to connect the upper terminal of comparator C_{sense} to either a source of voltage V_A or to the input **116** of comparator **304**. The input **116** is also connected to the upper (drain) terminal of transistor **240** which has its source terminal connected to the resistance element **204**, the resistance of which is to be measured.

All of the switch elements **134**, **136** and **206** switch together to either connect the upper terminals of capacitors C_{sense} , C_1 , and C_0 to the voltage V_A , or to connect the upper terminal of capacitor C_{sense} to input **116** and the upper terminals of capacitors C_1 and C_0 to common voltage line **132**. When the switch elements are in the latter condition the capacitors C_{sense} , C_1 , and C_0 are connected in a way which provides the current flows **10**, **11** and I_{sense} through respective resistance elements **R0**, **R1** and **204**.

The circuit of FIG. 3 operates as follows. Capacitors C_{sense} , C_1 , and C_0 are first fully charged to V_A by switch elements **134**, **136** and **206** simultaneously connecting their upper terminals to a V_A voltage source. After the capacitors C_{sense} , C_1 , and C_0 are charged the switch elements **134**, **136**, and **206** are simultaneously operated to connect the upper terminal of capacitor C_{sense} to input **116** and the upper terminal of capacitors C_0 and C_1 to the common voltage line **132**. As a result all three capacitors begin discharging in unison in the direction symbolized by current flow arrows I_{sense} , I_1 , and I_0 . The rate at which the capacitors C_1 and C_0 discharge is determined by the resistance of the path through which they discharge.

The capacitor C_{sense} will also discharge through resistance element **204** and the decaying voltage on capacitor **204**

is applied to sense voltage input **116** of comparator **304**. The discharge of both capacitors simultaneously will provide a reference voltage on voltage line **132** which is the average voltage instantaneously on capacitors C_1 , C_0 . Thus, as capacitors C_1 and C_0 discharge, this average voltage will decay. This average voltage is applied to the reference voltage input of comparator **304**. The capacitor C_{sense} will discharge significantly faster if resistance element **204** has a resistance representing a '0' value (e.g. 950 K Ω) than a resistance representing a '1' value (e.g. 1 M Ω). Consequently, the voltage on C_{sense} will discharge either more slowly or more quickly than the average voltage discharge of C_1 and C_0 , hereafter noted as V_{sense} . The combined average voltage across capacitors C_1 and C_0 as seen by comparator **304** decays with time as shown by V_{av} in FIG. 4. V_{av} falls between the decaying voltage on capacitor C_{sense} when a logical '1' and a '0' resistance is set in resistance element **204**. Because the resistive memory element **204** being sensed will either store a 1 or a 0, its discharge voltage V_{sense} will (intentionally) never be equal to V_{av} , instead V_{sense} will always be measurably higher or lower than V_{av} . Accordingly, the difference between the sensed and reference discharge voltages (V_{sense} and V_{av}) will be compared by the comparator **304** at sense time t_{sense} , which will provide an electrical '1' or '0' output representing the stored logic value of resistance element **204**.

Thus, determining whether a resistive memory element holds a '1' or a '0' does not require quantitatively measuring V_{sense} , instead, it is only necessary to compare V_{sense} with V_{av} using a comparator **304**. A circuit for comparing V_{sense} to V_{av} can be achieved with less components than a circuit for quantitatively measuring V_{sense} . The frequency with which the voltages V_{sense} and V_{av} can be compared is limited only by the capacitance values of C_0 , C_1 , and C_{sense} which must also produce an integrating effect across their respective resistance elements.

FIG. 5 shows an alternative embodiment in which only a single capacitor C_{av} is used in the reference voltage across **115a**. In such an embodiment, the desired V_{av} could be obtained by discharging capacitor C_{av} across a single resistor R_{median} of known value which lies between resistance values corresponding to a logical '0' and '1' value. For example, if 950 K Ω corresponds to a typical MRAM resistance for a binary '0', and 1 M Ω corresponds to the typical MRAM resistance for a binary '1', then a median resistance value is set for example at 975 K Ω . By discharging capacitor C_{av} across such a median resistance, a value for V_{av} for comparison with V_{sense} can be provided. In this embodiment, the R_{median} resistance can be provided by using a single column, e.g. **108**, of reference resistance elements in array **100** having this value, or dispensing with reference resistance element in the array in favor of an out-of-array reference resistance element which has the R_{median} value.

FIG. 6 illustrates how the current regulating circuit **200** and sensing circuit **300** of the invention are arranged with a memory array **100**. In FIG. 6, the columns which connect with storage resistive elements are labeled **107**, **109**, while the reference columns remain shown in **108**, **110**.

The sensing circuit **300** of the present invention compares two discharge voltages V_{sense} and V_{av} and immediately makes a determination which logical value to output on bit-out line **330**. Thus, a method and apparatus for quickly measuring MRAM values while minimizing the number of necessary components is achieved.

FIG. 7 is a block diagram of a processor-based system **350** utilizing a MRAM array **100** constructed in accordance with

one of the embodiments of the present invention. The processor-based system **350** may be a computer system, a process control system or any other system employing a processor and associated memory. The system **350** includes a central processing unit (CPU) **352**, e.g., a microprocessor, that communicates with the MRAM array **100** and an I/O device **354** over a bus **356**. It must be noted that the bus **356** may be a series of buses and bridges commonly used in a processor-based system, but for convenience purposes only, the bus **356** has been illustrated as a single bus. A second I/O device **306** is illustrated, but is not necessary to practice the invention. The processor-based system **350** also includes read-only memory (ROM) **360** and may include peripheral devices such as a floppy disk drive **362** and a compact disk (CD) ROM drive **364** that also communicates with the CPU **352** over the bus **356** as is well known in the art.

While the invention has been described and illustrated with reference to specific exemplary embodiments, it should be understood that many modifications and substitutions can be made without departing from the spirit and scope of the invention. Accordingly, the invention is not to be considered as limited by the foregoing description but is only limited by the scope of the appended claims.

What is claimed is:

1. A resistance memory device, comprising:
 - memory array comprising a plurality of row lines, a plurality of column lines, and a plurality of resistive elements, each resistive element connected to a row line and a column line, said resistive elements having one of a first resistance value which represents a first logical state and a second resistance value which represents a second logical state;
 - a sensing circuit for sensing the resistance value of a selected resistance element, said sensing circuit comprising:
 - a first capacitor and at least one second capacitor;
 - a charging circuit for charging said capacitors to a predetermined voltage value;
 - a reference resistance element;
 - a first discharge circuit for discharging said first capacitor through said selected resistive element and a second discharge circuit for discharging said at least one second capacitor through said reference resistance element; and
 - a comparison circuit for comparing a discharge characteristic of said first capacitor with a discharge characteristic of said at least one second capacitor.
2. The memory device of claim **1**, wherein said at least one second capacitor comprises a first and a second reference capacitor and said associated reference resistance element comprises first and a second resistance elements respectively associated with said first and second reference capacitances having resistance values respectively corresponding to a binary '1' value and a binary '0' value, wherein said first reference capacitor discharges through said first resistance element, and said second reference capacitor discharges through said second resistance element.
3. The memory device as in claim **1** or **2** wherein said comparison circuit compares the voltage levels of said first and at least one second capacitor during the discharging of said capacitors.
4. The memory device of claim **1**, further comprising:
 - a regulation circuit for maintaining a predetermined voltage across said selected resistance element and said reference resistance element during discharge of said capacitors.
5. The memory device of claim **4** wherein said regulation circuit comprises a first regulator associated with said

selected resistance element and at least one second regulator associated with said reference resistance.

6. The memory device of claim **1**, wherein said charging circuit further comprises a switch circuit for selectively connecting said first and at least one second capacitor to a source providing said predetermined voltage value and resistance.

7. The memory device of claim **6** wherein said at least one second capacitor comprises a first reference capacitor and said associated reference resistance element comprises a first reference resistance element, said first reference resistance element having a resistance value which resides between two possible resistance values for said selected resistance element, said comparison circuit comprising a discharging voltage of said first reference capacitor with a discharge voltage of said first capacitor.

8. The memory device of claim **1** wherein said memory array is an MRAM memory array.

9. An MRAM memory device, comprising:

- a memory array comprising a plurality of row lines, a plurality of column lines, and a plurality of resistive elements, each resistive element connected to a row line and a column line, said resistive elements having one of a first resistance value which represents a first logical state and a second resistance value which represents a second logical state;

- a sensing circuit for sensing the resistance value of a selected resistance element, said sensing circuit comprising:

- a first capacitor and at least one second capacitor;
- a charging circuit for charging said capacitors to a predetermined voltage value;
- a reference resistance element;
- a first discharge circuit for discharging said first capacitor through said selected resistive element and a second discharge circuit for discharging said at least one second capacitor through said reference resistance element; and

- a comparison circuit for comparing a discharge characteristic of said first capacitor with a discharge characteristic of said at least one second capacitor.

10. The MRAM memory device of claim **9**, wherein said at least one second capacitor comprises a first and a second reference capacitor and said associated reference resistance element comprises first and a second resistance elements respectively associated with said first and second reference capacitances having resistance values respectively corresponding to a binary '1' value and a binary '0' value, wherein said first reference capacitor discharges through said first resistance element, and said second reference capacitor discharges through said second resistance element.

11. The MRAM memory device as in claim **9** or **10** wherein said comparison circuit compares the voltage levels of said first and at least one second capacitor during the discharging of said capacitors.

12. The MRAM memory device of claim **9**, further comprising:

- a regulation circuit for maintaining a predetermined voltage across said selected resistance element and said reference resistance element during discharge of said capacitors.

13. The MRAM memory device of claim **12** wherein said regulation circuit comprises a first regulator associated with said selected resistance element and at least one second regulator associated with said reference resistance.

14. The MRAM memory device of claim **9**, wherein said charging circuit further comprises a switch circuit for selec-

tively connecting said first and at least one second capacitor to a source providing said predetermined voltage value and resistance.

15. The MRAM memory device of claim 14 wherein said at least one second capacitor comprises a first reference capacitor and said associated reference resistance element comprises a first reference resistance element, said first reference resistance element having a resistance value which resides between two possible resistance values for said selected resistance element, said comparison circuit comprising a discharging voltage of said first reference capacitor with a discharge voltage of said first capacitor.

16. A method of reading a resistance array, comprising a plurality of column lines, a plurality of row lines, and plurality of resistance elements each connected to a column and row line:

grounding a selected row of said arrays which contain resistance elements to be read;

holding all other rows of said array at a specific voltage;

pre-setting the resistance of a first resistance element connected to said grounded row and associated with a first reference column line to hold a binary '1' resistance value;

pre-setting the resistance of a second resistance element connected to said grounded row and associated with a second reference column line to hold a binary '0' resistance value;

charging a first capacitor associated with a column line of said selected resistance element to a first voltage value;

charging first and second reference capacitors respectively associated with said first and second reference resistance elements to said first voltage value;

discharging said first capacitor through said selected resistance element while discharging said first and second reference capacitors respectively through said first and second resistance elements;

comparing the discharge voltage of said first capacitor with a discharge voltage formed by the discharge rates of said first and second reference capacitors;

determining the binary value held within said selected resistance element as a result of said comparison.

17. The method of claim 16, further comprising:

holding one terminal of said selected resistance element to be read at a constant voltage using the discharge of said first capacitor.

18. The method of claim 16, further comprising:

holding one terminal of first and second reference resistance elements at said constant array voltage using the discharge of said first and second reference capacitors.

19. A method of reading a resistance array, comprising a plurality of column lines, a plurality of row lines, and plurality of resistance elements each connected to a column and row line:

grounding a selected row of said arrays which contain resistance elements to be read;

holding all other rows of said array at a specific voltage;

pre-setting the resistance of a reference resistance element connected to said grounded row and associated with a first reference column line to reside directly between a binary '1' and a binary '0' resistance value;

charging a first capacitor associated with a column line of said selected resistance element to a first voltage value;

charging a first reference capacitor associated with said reference resistance element to said first voltage value;

discharging said first capacitor through said selected resistance element while discharging said first reference capacitor through said reference resistance element;

comparing the discharge voltage of said first capacitor with a discharge voltage formed by the discharge rates of said first reference capacitor;

determining the binary value held within said selected resistance element as a result of said comparison.

20. The method of claim 19, further comprising:

holding one terminal of said selected resistance element to be read at a constant voltage using the discharge of said first capacitor.

21. The method of claim 19, further comprising:

holding one terminal of first and second reference resistance elements at said constant array voltage using the discharge of said first and second reference capacitors.

22. A processor circuit, comprising:

a CPU;

an resistive memory circuit, further comprising:

a memory array comprising a plurality of row lines, a plurality of column lines, and a plurality of resistive elements, each resistive element connected to a row line and a column line, said resistive elements having one of a first resistance value which represents a first logical state and a second resistance value which represents a second logical state;

a sensing circuit for sensing the resistance value of a selected resistance element, said sensing circuit comprising:

a first capacitor and at least one second capacitor;

a charging circuit for charging said capacitors to a predetermined voltage value;

a reference resistance element;

a first discharge circuit for discharging said first capacitor through said selected resistive element and a second discharge circuit for discharging said at least one second capacitor through said reference resistance element; and

a comparison circuit for comparing a discharge characteristic of said first capacitor with a discharge characteristic of said at least one second capacitor.

23. The processor circuit of claim 22, wherein said at least one second capacitor comprises a first and a second reference capacitor and said associated reference resistance element comprises first and a second resistance elements respectively associated with said first and second reference capacitances having resistance values respectively corresponding to a binary '1' value and a binary '0' value, wherein said first reference capacitor discharges through said first resistance element, and said second reference capacitor discharges through said second resistance element.

24. The processor circuit as in claims 22 or 23 wherein said comparison circuit compares the voltage levels of said first and at least one second capacitor during the discharging of said capacitors.

25. The processor circuit of claim 22, further comprising:

a regulation circuit for maintaining a predetermined voltage across said selected resistance element and said reference resistance element during discharge of said capacitors.

26. The processor circuit of claim 25 wherein said regulation circuit comprises a first regulator associated with said selected resistance element and at least one second regulator associated with said reference resistance.

27. The processor circuit of claim 22, wherein said charging circuit further comprises a switch circuit for selec-

tively connecting said first and at least one second capacitor to a source providing said predetermined voltage value and resistance.

28. The processor circuit of claim 27 wherein said at least one second capacitor comprises a first reference capacitor and said associated reference resistance element comprises a first reference resistance element, said first reference resistance element having a resistance value which resides between two possible resistance values for said selected resistance element, said comparison circuit comprising a discharging voltage of said first reference capacitor with a discharge voltage of said first capacitor.

29. An processor circuit, comprising:

a CPU;

an MRAM memory circuit, further comprising:

a memory array comprising a plurality of row lines, a plurality of column lines, and a plurality of resistive elements, each resistive element connected to a row line and a column line, said resistive elements having one of a first resistance value which represents a first logical state and a second resistance value which represents a second logical state;

a sensing circuit for sensing the resistance value of a selected resistance element, said sensing circuit comprising:

a first capacitor and at least one second capacitor; a charging circuit for charging said capacitors to a predetermined voltage value;

a reference resistance element;

a first discharge circuit for discharging said first capacitor through said selected resistive element and a second discharge circuit for discharging said at least one second capacitor through said reference resistance element; and

a comparison circuit for comparing a discharge characteristic of said first capacitor with a discharge characteristic of said at least one second capacitor.

30. The processor circuit of claim 29, wherein said at least one second capacitor comprises a first and a second refer-

ence capacitor and said associated reference resistance element comprises first and a second resistance elements respectively associated with said first and second reference capacitances having resistance values respectively corresponding to a binary '1' value and a binary '0' value, wherein said first reference capacitor discharges through said first resistance element, and said second reference capacitor discharges through said second resistance element.

31. The processor circuit as in claim 29 or 30 wherein said comparison circuit compares the voltage levels of said first and at least one second capacitor during the discharging of said capacitors.

32. The processor circuit of claim 29, further comprising:

a regulation circuit for maintaining a predetermined voltage across said selected resistance element and said reference resistance element during discharge of said capacitors.

33. The processor circuit of claim 32 wherein said regulation circuit comprises a first regulator associated with said selected resistance element and at least one second regulator associated with said reference resistance.

34. The processor circuit of claim 29, wherein said charging circuit further comprises a switch circuit for selectively connecting said first and at least one second capacitor to a source providing said predetermined voltage value and resistance.

35. The processor circuit of claim 34 wherein said at least one second capacitor comprises a first reference capacitor and said associated reference resistance element comprises a first reference resistance element, said first reference resistance element having a resistance value which resides between two possible resistance values for said selected resistance element, said comparison circuit comprising a discharging voltage of said first reference capacitor with a discharge voltage of said first capacitor.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,577,525 B2
DATED : June 10, 2003
INVENTOR(S) : R. J. Baker

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 3,

Line 41, change "it" to -- its --

Column 4,

Line 13, change " V_{sense} ," to -- V_{av} , --

Column 5,

Line 25, change "memory" to -- a memory --

Column 6,

Line 8, change "on" to -- one --

Column 7,

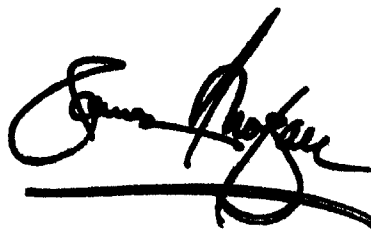
Line 5, change "on" to -- one --

Column 10,

Line 30, change "on" to -- one --

Signed and Sealed this

Twenty-third Day of September, 2003

A handwritten signature in black ink, appearing to read "James E. Rogan", written over a horizontal line.

JAMES E. ROGAN
Director of the United States Patent and Trademark Office

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,577,525 B2
DATED : June 10, 2003
INVENTOR(S) : R.J. Baker

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Drawings,

Figure 3, upper right, reads "120" should read -- 300 --

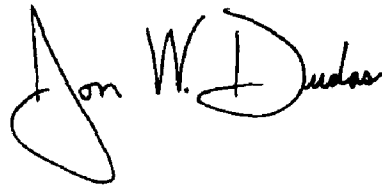
Figure 3, center reads "204" should read -- 244 --.

Column 3,

Line 15, reads "204" should read -- 244 --.

Signed and Sealed this

Twenty-fourth Day of August, 2004

A handwritten signature in black ink that reads "Jon W. Dudas". The signature is written in a cursive style with a large, looped initial "J".

JON W. DUDAS
Director of the United States Patent and Trademark Office

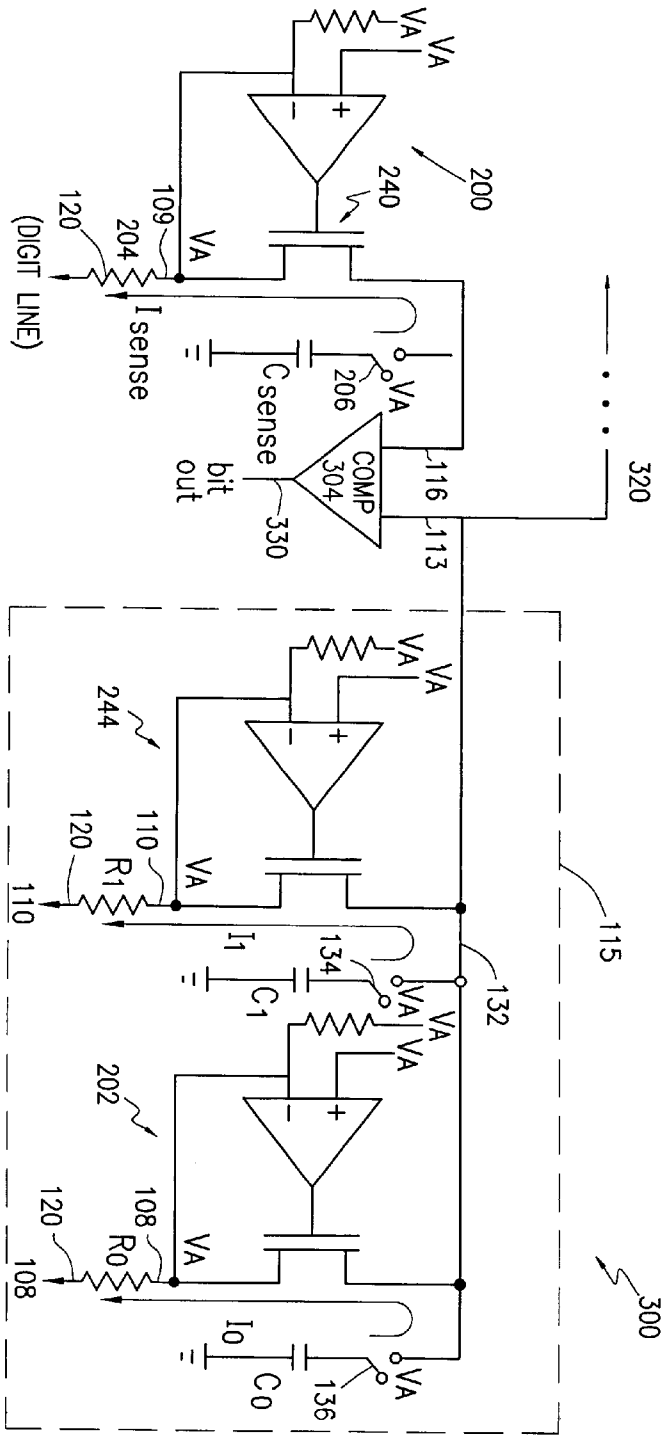


FIG. 3